

- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

Product Summary

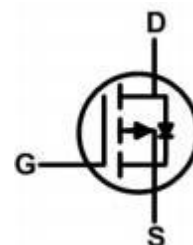


BVDSS	RDSON	ID
-40V	3.5mΩ	-150A

Description

The XR150P04 is the high cell density trench P-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications. The XR150P04 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

TO252-3L Pin Configuration



Absolute Maximum Ratings (T_C=25°C unless otherwise noted)

Symbol	Parameter	Limit	Unit
V _{DS}	Drain-Source Voltage (V _{GS} =0V)	-40	V
V _{GS}	Gate-Source Voltage (V _{DS} =0V)	±20	V
I _D	Drain Current-Continuous(T _C =25°C)	-150	A
	Drain Current-Continuous(T _C =100°C)	-104	A
I _{DM} (pluse)	Drain Current-Continuous@ Current-Pulsed (Note 1)	-592	A
P _D	Maximum Power Dissipation(T _C =25°C)	200	W
	Maximum Power Dissipation(T _C =100°C)	100	W
E _{AS}	Avalanche energy (Note 2)	1225	mJ
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 To 175	°C

Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
R _{θJC}	Thermal Resistance, Junction-to-Case		0.95	°C/W

Electrical Characteristics (T_J=25°C unless otherwise noted)

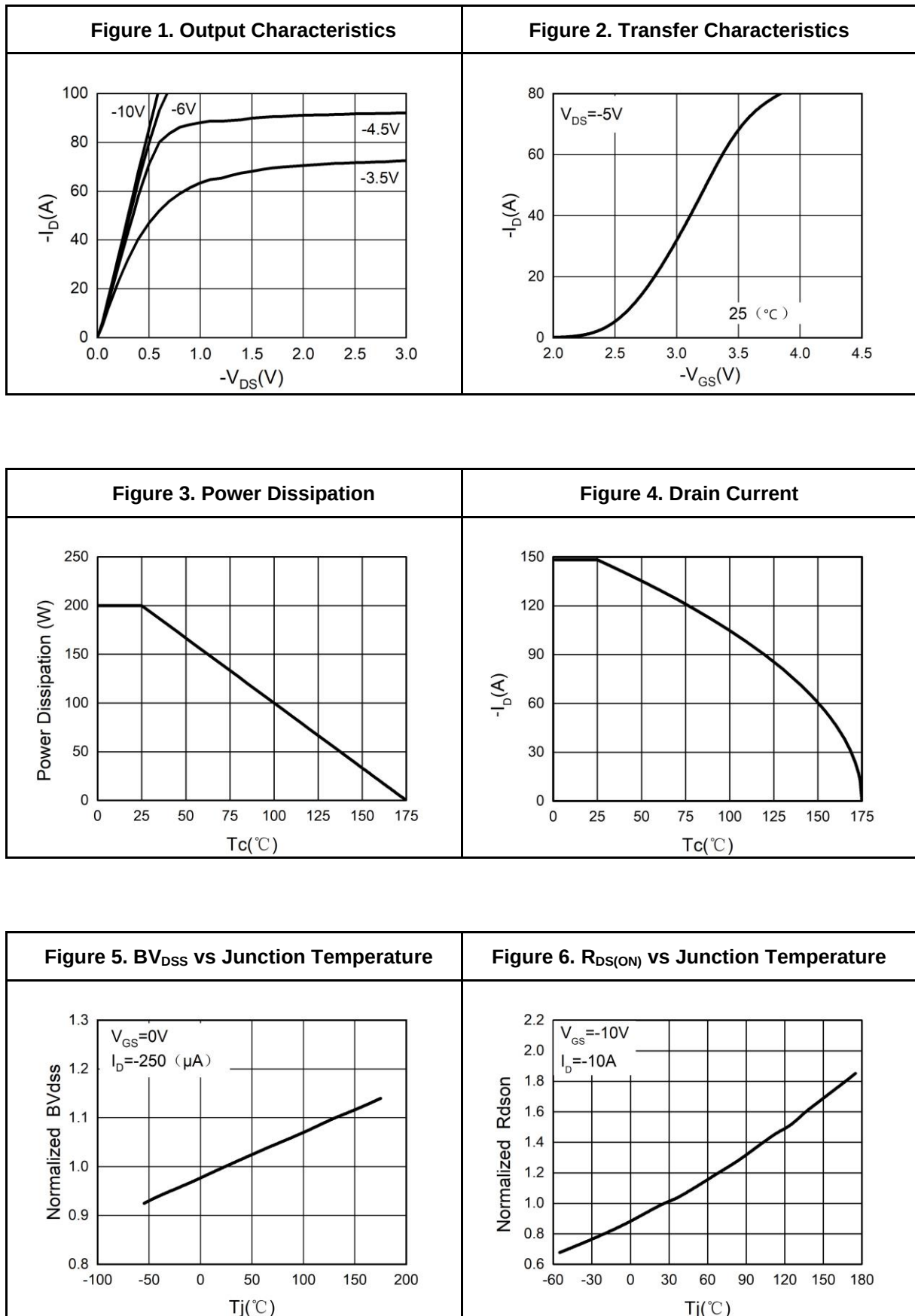
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V I _D =-250μA	-40			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-40V, V _{GS} =0V T _J =25℃			-1	μA
		V _{DS} =-40V, V _{GS} =0V T _J =125℃			-100	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-1		-2.5	V
g _{FS}	Forward Transconductance	V _{DS} =-10V, I _D =-20A		51		S
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =-10V, I _D =-20A T _J =25℃		3.5	4.5	mΩ
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =-4.5V, I _D =-20A T _J =25℃		4.8	6	mΩ
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =-20V,V _{GS} =0V, f=1.0MHz		10733		pF
C _{oss}	Output Capacitance			770		pF
C _{rss}	Reverse Transfer Capacitance			697		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1.0MHz		1.7		Ω
Switching Parameters						
t _{d(on)}	Turn-on Delay Time	V _{GS} =-10V, V _{DS} =-20V, R _L =1Ω, R _{GEN} =3Ω		19.6		nS
t _r	Turn-on Rise Time			3.6		nS
t _{d(off)}	Turn-Off Delay Time			22.8		nS
t _f	Turn-Off Fall Time			38		nS
Q _g	Total Gate Charge	V _{GS} =-10V, V _{DS} =-20V, I _D =-20A		195		nC
Q _{gs}	Gate-Source Charge			24.1		nC
Q _{gd}	Gate-Drain Charge			39.9		nC
Source-Drain Diode Characteristics						
I _{SD}	Source-Drain Current (Body Diode)				-150	A
V _{SD}	Forward on Voltage (Note 3)	V _{GS} =0V, I _S =-20A			-1.2	V
t _{rr}	Reverse Recovery Time	I _F =-20A, dI/dt=-100A/μs		51.1		ns
Q _{rr}	Reverse Recovery Charge	I _F =-20A, dI/dt=-100A/μs		125.2		nC

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature.

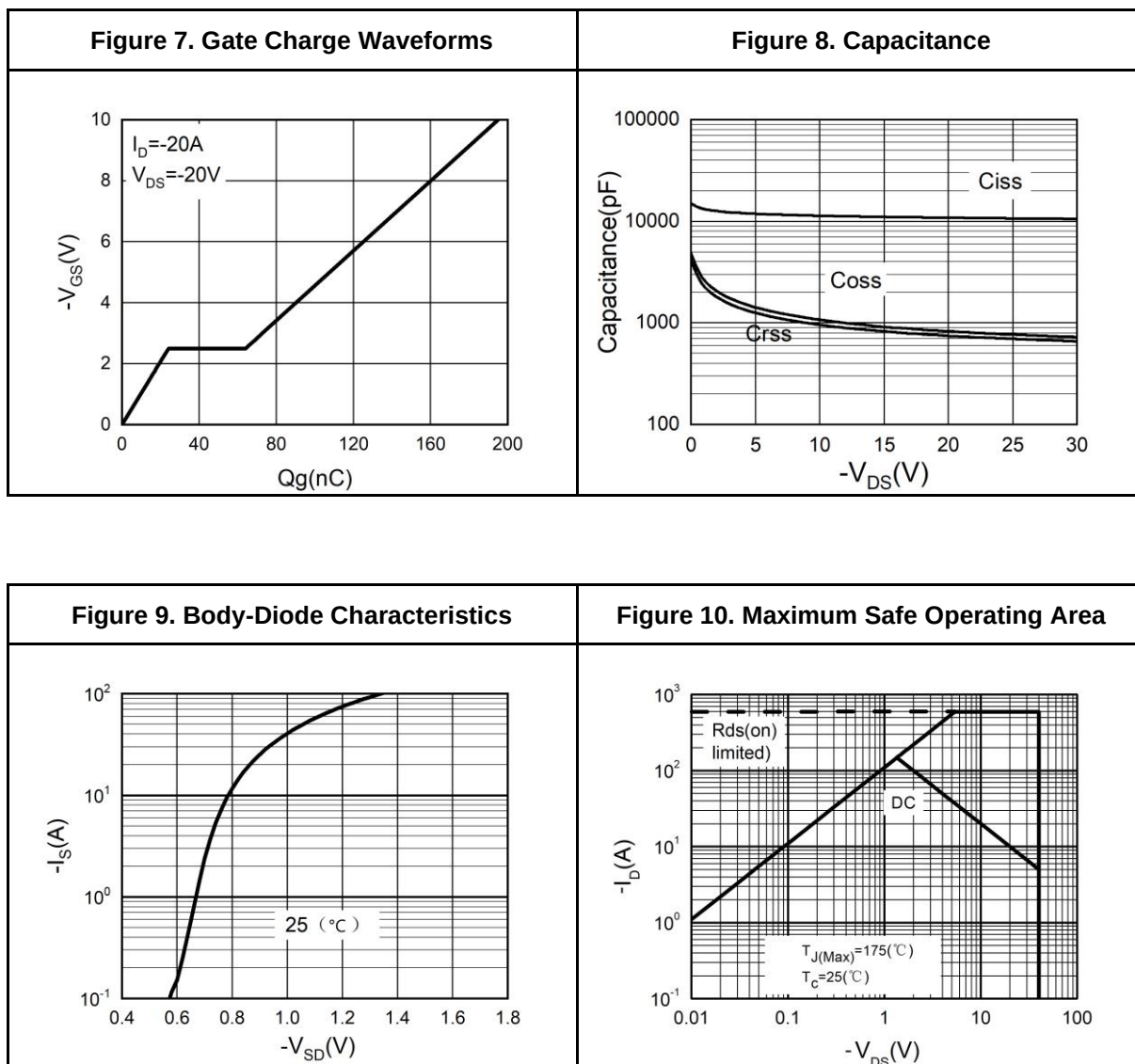
Notes 2.EAS condition: T_J=25°C, V_{DD}=-40V, V_G=-10V, R_g=25Ω, L=0.5mH.

Notes 3.Repetitive Rating: Pulse width limited by maximum junction temperature.

Typical Electrical And Thermal Characteristics (Curves)



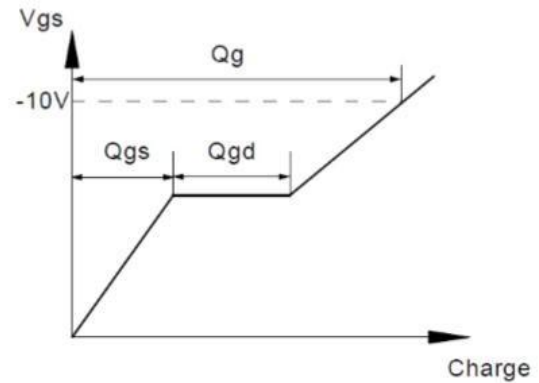
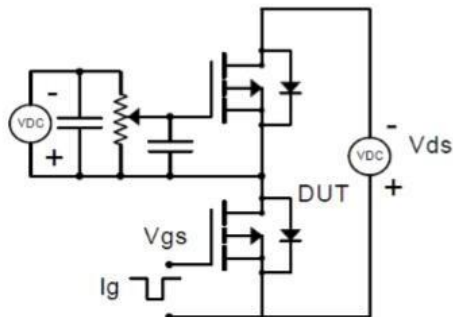
Typical Electrical And Thermal Characteristics (Curves)



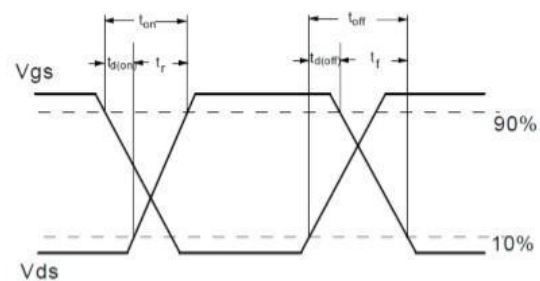
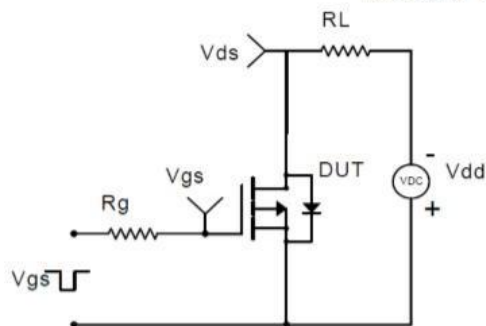
Test Circuit

P-Ch 40V Fast Switching MOSFETs

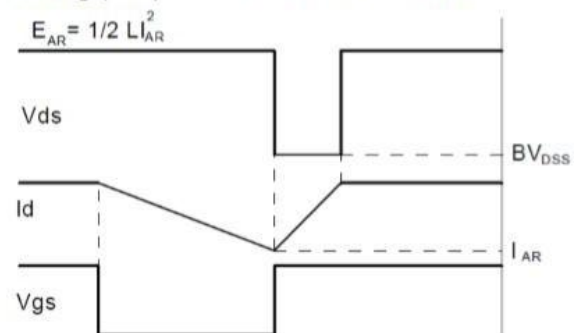
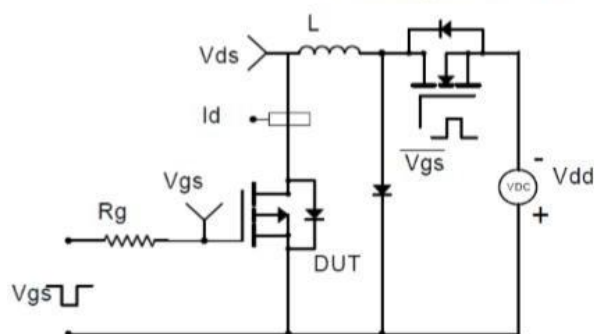
Gate Charge Test Circuit & Waveform



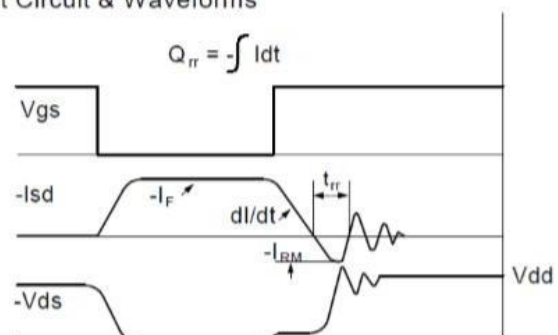
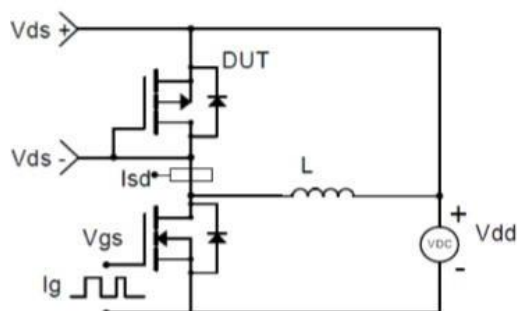
Resistive Switching Test Circuit & Waveforms



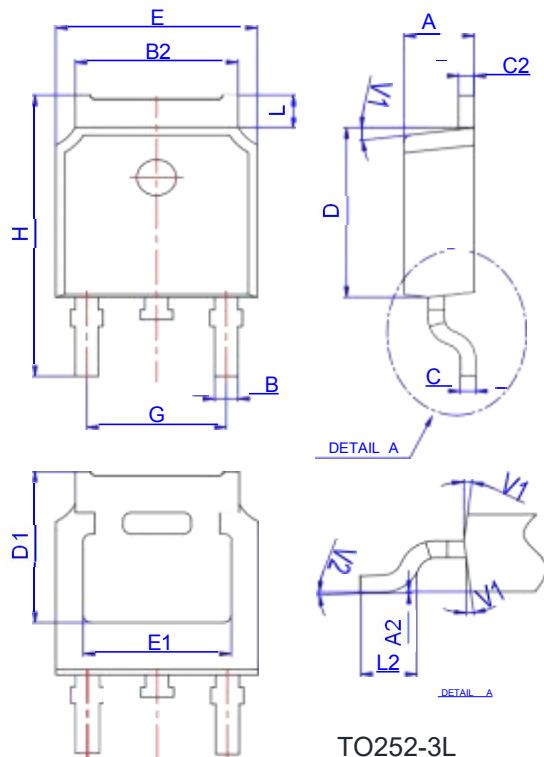
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

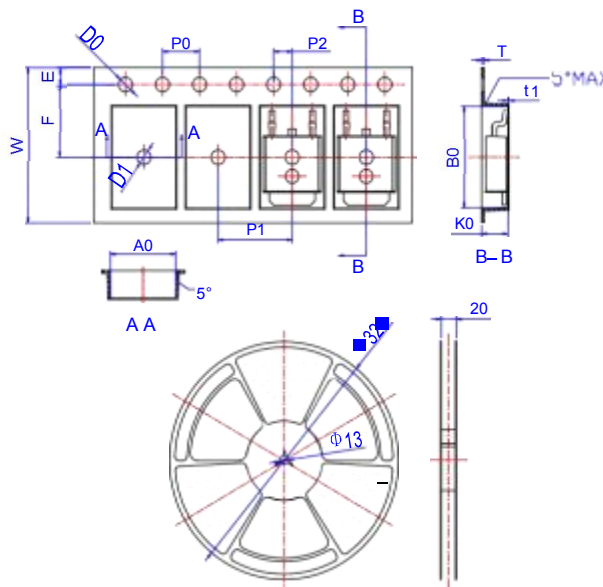


Package Mechanical Data-TO252-3L



Ref.	Dimensions					
	Millimeters			Inches		
	Min .	Typ .	Max.	Min .	Typ .	Max .
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Lead Specification-TO252-3L



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583